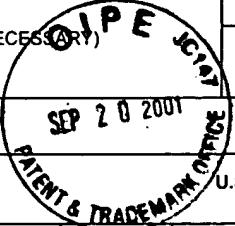


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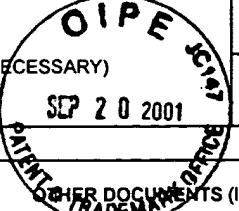
**U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
A.M.	3 Dücsö, C. et al., <i>Research Institute for materials Science – ATKI, H-1525 Budapest, Hungary</i> , Utriainen, M. et al., <i>Laboratory of Inorganic and Analytical Chemistry, Helsinki University of Technology, FIN-02150 Espoo, Finland</i> , "Deposition of Tin Oxide into Porous Silicon by Atomic Layer Epitaxy," <i>J. Electrochemical Society</i> , Vol. 143, No. 2, pp. 683-687 (1996).
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)		
A.M	14	Ritala, M. et al., "Conformal TiN and Al <sub>2</sub> O <sub>3</sub> Films Deposited by Atomic Layer Deposition," <u>Chemical Vapor Deposition</u> , Vol. 5, No. 1, pp. 7-9 (1999).	
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